ABSTRACT OF THE DISCLOSURE

A pattern forming method includes: forming an etching-subject layer on a substrate; forming a Ti layer on the etching-subject layer; forming a TiOx layer by irradiating light on a portion of the Ti layer using a mask; etching the Ti layer to form a TiOx pattern; etching the etching-subject layer using the TiOx pattern as a mask; and removing the TiOx pattern.

1-WA/2024007.1 36